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Attorney Docket 040301-0578



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Nobutoshi AOKI et al.

Title: SEMICONDUCTOR INTEGRATED CIRCUIT INCLUDING INSULATED GATE  
FIELD EFFECT TRANSISTOR AND METHOD OF MANUFACTURING THE  
SAME

Appl. No.: 09/440,928

Filing Date: 11/16/1999

Examiner: S. Rao

Art Unit: 2814

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AMENDMENT TRANSMITTAL

Commissioner for Patents  
Washington, D.C. 20231

Sir:

Transmitted herewith is a Supplemental Preliminary Amendment in the above-identified application.

- ☐ Small Entity status under 37 C.F.R. § 1.9 and § 1.27 has been established by a Small Entity statement previously submitted.
- ☐ Small Entity statement is enclosed.
- ☒ The fee required for additional claims is calculated below:

	Claims as Amended	Previously Paid For	Extra Claims Present	Rate	Additional Claims Fee
Total Claims:	28	26	2	x \$18.00	\$36.00
Independents:	8	6	2	x \$84.00	\$168.00
First presentation of any Multiple Dependent Claims:				+ \$280.00	\$0.00
CLAIMS FEE TOTAL:					\$204.00

- ☐ Applicant hereby petitions for an extension of time under 37 C.F.R. § 1.136(a) for the total number of months checked below:

<input type="checkbox"/>	Extension for response filed within the first month:	\$110.00	\$0.00
<input type="checkbox"/>	Extension for response filed within the second month:	\$400.00	\$0.00
<input type="checkbox"/>	Extension for response filed within the third month:	\$920.00	\$0.00
<input type="checkbox"/>	Extension for response filed within the fourth month:	\$1,440.00	\$0.00
<input type="checkbox"/>	Extension for response filed within the fifth month:	\$1,960.00	\$0.00
EXTENSION FEE TOTAL:			\$0.00
CLAIMS AND EXTENSION FEE TOTAL:			\$204.00
<input type="checkbox"/>	Small Entity Fees Apply (subtract ½ of above):		\$0.00
TOTAL FEE:			\$204.00

- ☐ Please charge Deposit Account No. 19-0741 in the amount of \$204.00. A duplicate copy of this transmittal is enclosed.
- ☒ A check in the amount of \$204.00 is enclosed.
- ☒ The Commissioner is hereby authorized to charge any additional fees which may be required regarding this application under 37 C.F.R. §§ 1.16-1.17, or credit any overpayment, to Deposit Account No. 19-0741. Should no proper payment be enclosed herewith, as by a check being in the wrong amount, unsigned, post-dated, otherwise improper or informal or even entirely missing, the Commissioner is authorized to charge the unpaid amount to Deposit Account No. 19-0741.

Please direct all correspondence to the undersigned attorney or agent at the address indicated below.

Respectfully submitted,

Date December 3, 2002

By Aaron C. Chatterjee

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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M. Brunson  
12/19/02

Applicant: Nobutoshi AOKI et al.

Title: SEMICONDUCTOR INTEGRATED CIRCUIT INCLUDING  
INSULATED GATE FIELD EFFECT TRANSISTOR AND METHOD  
OF MANUFACTURING THE SAME

Appl. No.: 09/440,928

Filing Date: November 16, 1999

Examiner: S. Rao

Art Unit: 2814

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**SUPPLEMENTAL PRELIMINARY AMENDMENT**

Commissioner for Patents  
Washington, D.C. 20231

Sir:

Prior to further examination of the present application and supplemental to the Preliminary Amendment filed November 19, 2002, applicants respectfully request that the above-identified application be further amended as follows:

**IN THE CLAIMS:**

Please amend the claims by replacing the indicated claims with the following clean version. (See Attachment A for the marked up version of the amended claims.)

- FI
1. (Four Times Amended) A semiconductor device comprising:  
a pair of main electrodes used as source and drain electrodes;  
a channel forming region provided between the pair of main electrodes;  
an insulating gate film formed on the channel forming region; and  
a gate electrode formed on the insulating gate film, and provided with a first region including at least a first group IV element and a second group IV element and formed in contact with the insulating gate film, and a second region including the first group IV element

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